

sub-picoamp instrumentation or any high impedance signal sources. Sourced from Process 53.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{DG}$	Drain-Gate Voltage	40	V
V <sub>GS</sub>	Gate-Source Voltage	- 40	V
$I_{GF}$	Forward Gate Current	50	mA
T <sub>J</sub> ,T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	l I	Units	
		PN4117-4119	*MMBF4117-4119	
PD	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

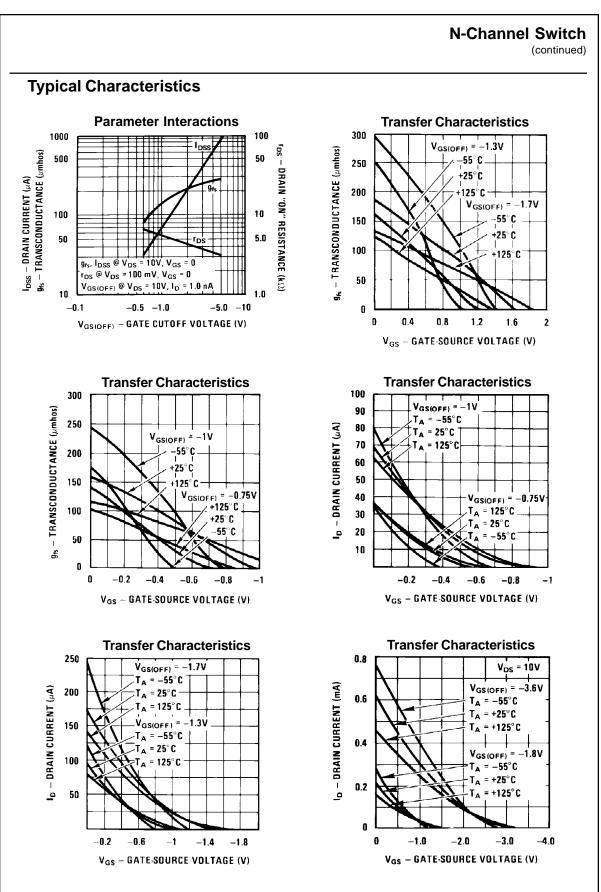
\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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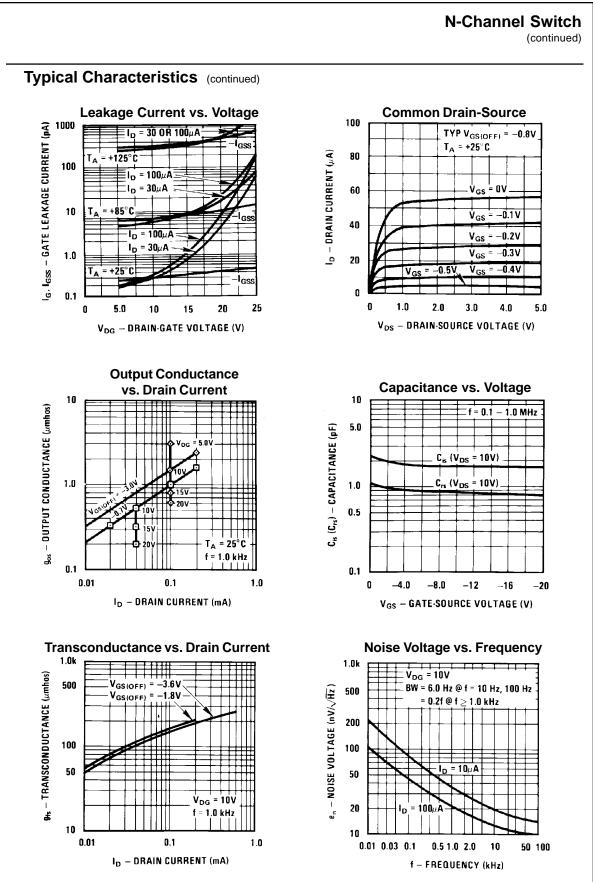
# N-Channel Switch (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS				
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	I <sub>G</sub> = - 1.0 μA, V <sub>DS</sub> = 0	- 40	T	V
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = -20 V, V_{DS} = 0$ $V_{GS} = -20 V, V_{DS} = 0, T_A = 150^{\circ}C$		- 10 - 25	pA nA
V <sub>GS(off)</sub>	Gate-Source Cutoff Voltage	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = 1.0 nA 4117 4118 4119	- 0.6 - 1.0 - 2.0	- 1.8 - 3.0 - 6.0	V V V
	ACTERISTICS Zero-Gate Voltage Drain Current*	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 4117 4118	30 80	90 240	μA μA
					•
IDSS SMALL-S	Zero-Gate Voltage Drain Current*	4118 4119	80	240	μA
IDSS SMALL-S	Zero-Gate Voltage Drain Current*	4118 4119 V <sub>DS</sub> = 10 V V <sub>GS</sub> = 0, f= 1.0 kHz 4117	80 200 70	240 600 210	μΑ μΑ μM
IDSS SMALL-S	Zero-Gate Voltage Drain Current* IGNAL CHARACTERISTICS Common-Source Forward	4118 4119 V <sub>DS</sub> = 10 V V <sub>GS</sub> = 0, f= 1.0 kHz	80 200	240 600	μΑ μΑ
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current* IGNAL CHARACTERISTICS Common-Source Forward	4118 4119 V <sub>DS</sub> = 10 V V <sub>GS</sub> = 0, f= 1.0 kHz 4117 4118	80 200 70 80	240 600 210 250	μΑ μΑ μmhos μmhos
I <sub>DSS</sub> SMALL-S gfs	Zero-Gate Voltage Drain Current* IGNAL CHARACTERISTICS Common-Source Forward Transconductance Common-Source Output	$\begin{array}{c} \mbox{4118} \\ \mbox{4119} \end{array}$ $V_{DS} = 10 \mbox{ V}_{GS} = 0, \mbox{ f= } 1.0 \mbox{ kHz} \\ \mbox{4117} \\ \mbox{4118} \\ \mbox{4119} \end{array}$ $V_{DS} = 10 \mbox{ V}_{GS} = 0, \mbox{ f= } 1.0 \mbox{ kHz} \end{array}$	80 200 70 80	240 600 210 250 330	μΑ μΑ μΑ μmhos μmhos μmhos μmhos μmhos
I <sub>DSS</sub> SMALL-S gfs	Zero-Gate Voltage Drain Current* IGNAL CHARACTERISTICS Common-Source Forward Transconductance Common-Source Output Conductance Common-Source Forwad	$\begin{array}{c} & 4118 \\ & 4119 \\ \hline \\ V_{DS} = 10 \ V \ V_{GS} = 0, \ f = 1.0 \ \text{kHz} \\ & 4117 \\ & 4118 \\ & 4119 \\ \hline \\ V_{DS} = 10 \ V \ V_{GS} = 0, \ f = 1.0 \ \text{kHz} \\ & 4117 \\ & 4118 \\ & 4119 \\ \hline \\ V_{DS} = 10 \ V, \ V_{GS} = 0, \ f = 30 \ \text{MHz} \\ \end{array}$	80 200 70 80 100	240 600 210 250 330 3.0 5.0	μ μ μ μ μ h os μ m hos μ m hos μ m hos
I <sub>DSS</sub> SMALL-S gfs goss	Zero-Gate Voltage Drain Current* IGNAL CHARACTERISTICS Common-Source Forward Transconductance Common-Source Output Conductance	$\begin{array}{c} \mbox{4118} \\ \mbox{4119} \end{array}$ $V_{DS} = 10 \ V \ V_{GS} = 0, \ f = 1.0 \ \text{kHz} \\ \mbox{4117} \\ \mbox{4118} \\ \mbox{4119} \end{array}$ $V_{DS} = 10 \ V \ V_{GS} = 0, \ f = 1.0 \ \text{kHz} \\ \mbox{4117} \\ \mbox{4118} \\ \mbox{4119} \end{array}$ $V_{DS} = 10 \ V, \ V_{GS} = 0, \ f = 30 \ \text{MHz} \\ \mbox{4117} \\ \mbox{4118} \\ \mbox{4118} \\ \mbox{4118} \end{array}$	80 200 70 80 100 60 70	240 600 210 250 330 3.0 5.0	μΑ μΑ μΑ μmhos μmhos μmhos μmhos μmhos
I <sub>DSS</sub> SMALL-S gfs goss	Zero-Gate Voltage Drain Current* IGNAL CHARACTERISTICS Common-Source Forward Transconductance Common-Source Output Conductance Common-Source Forwad	$\begin{array}{c} & 4118 \\ & 4119 \\ \hline \\ V_{DS} = 10 \ V \ V_{GS} = 0, \ f = 1.0 \ \text{kHz} \\ & 4117 \\ & 4118 \\ & 4119 \\ \hline \\ V_{DS} = 10 \ V \ V_{GS} = 0, \ f = 1.0 \ \text{kHz} \\ & 4117 \\ & 4118 \\ & 4119 \\ \hline \\ V_{DS} = 10 \ V, \ V_{GS} = 0, \ f = 30 \ \text{MHz} \\ & 4117 \\ \hline \end{array}$	80 200 70 80 100 60	240 600 210 250 330 3.0 5.0	μΑ μΑ μΑ μhos μmhos μmhos μmhos μmhos μmhos

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